KSD26N15

150V N-Channel MOSFET

General Description

The KSD26N15 combines advanced MOSFET technology with a low resistance package to provide extremely low $R_{DS}(ON)$.

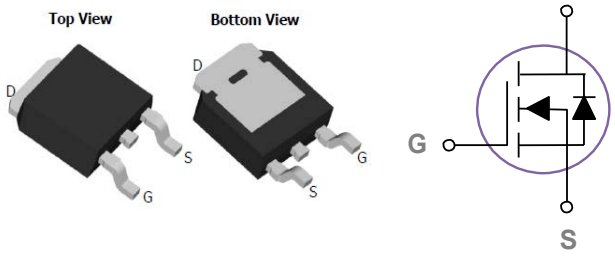
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)
150	48 at V_{GS} = 10 V	26
	54 at V_{GS} = 4.5 V	20

Features

- Advanced Power MOSFET technology
- Low $R_{DS}(ON)$
- Low Gate Charge
- Optimized for fast-switching applications

TO-252 Pin Configuration



Applications

- DC/DC power supplies
- Power Management for SMPS

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	26	A
	Drain Current – Continuous (T_C=100℃)	15.4	A
I_{DM}	Drain Current – Pulsed[1]	75	A
P_D	Power Dissipation (T_C=25℃)	70	W
	Power Dissipation (T_C=100℃)	1.2	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	63	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.36	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=60V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=10A	---	48	62	mΩ
		V_{GS}=4.5V , I_D=8A	---	54	69	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	2.0	3.4	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.2	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_S=8A	---	20	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=60V , V_{GS}=10V , I_D=8A	---	19	---	nC
Q_{gs}	Gate-Source Charge[2,3]		---	7	---	
Q_{gd}	Gate-Drain Charge[2,3]		---	3.6	---	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=60V, I_D=8A V_{GS}=10V,R_G=4.5Ω	---	9	---	ns
T_r	Rise Time[2,3]		---	32	---	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	18	---	
T_f	Fall Time[2,3]		---	27	---	
C_{iss}	Input Capacitance	V_{DS}=60V , V_{GS}=0V , F=1MHz	---	1090	---	pF
C_{oss}	Output Capacitance		---	71	---	
C_{rss}	Reverse Transfer Capacitance		---	30	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	26	A
I_{SM}	Pulsed Source Current		---	---	50	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristics (Curves)

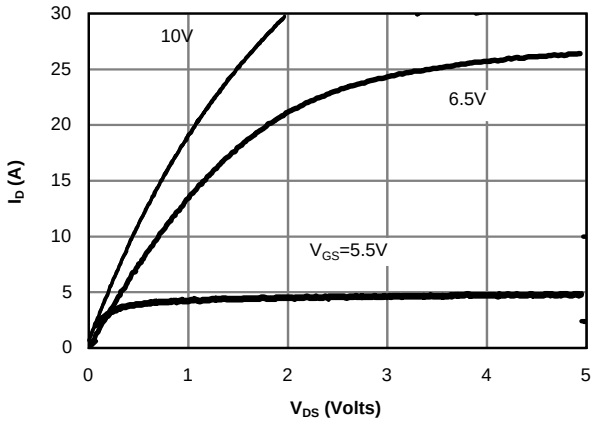


Fig 1: On-Region Characteristics (Note E)

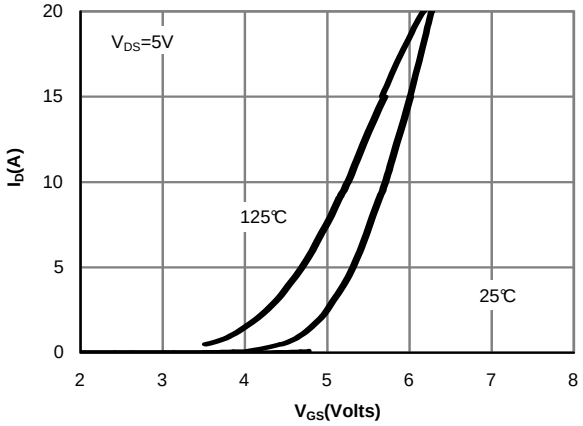


Figure 2: Transfer Characteristics (Note E)

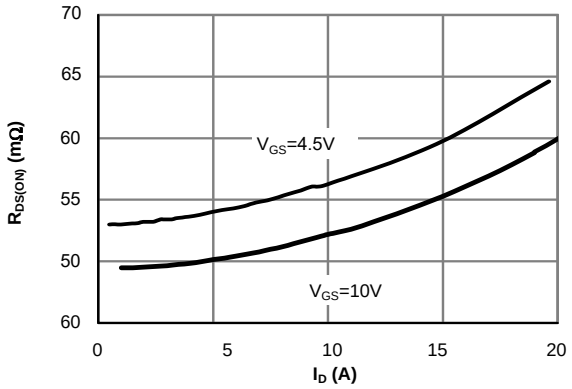


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

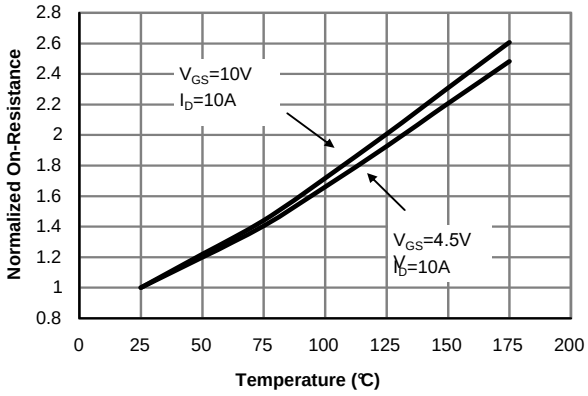


Figure 4: On-Resistance vs. Junction Temperature(Note E)

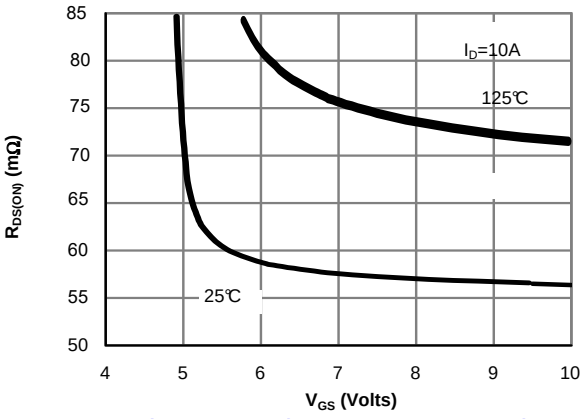


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

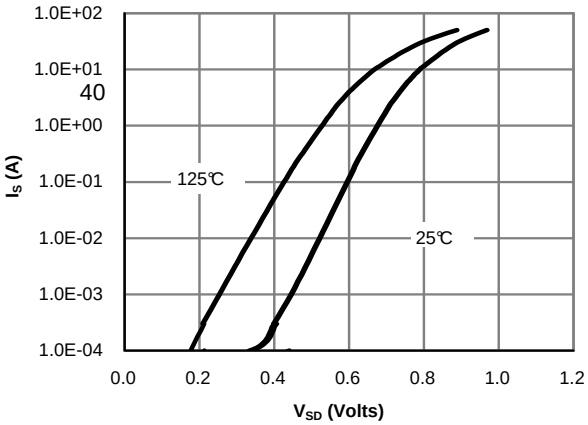


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

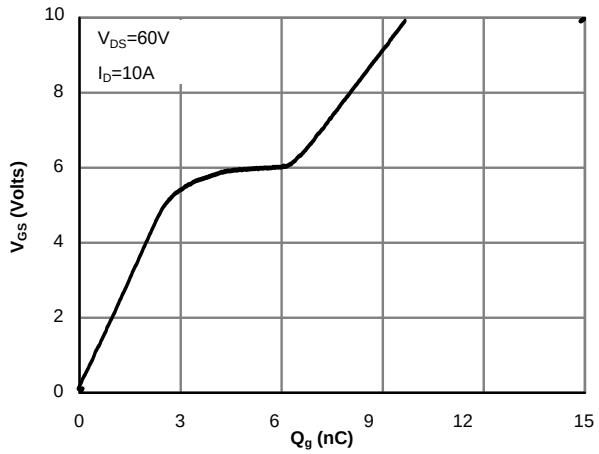


Figure 7: Gate-Charge Characteristics

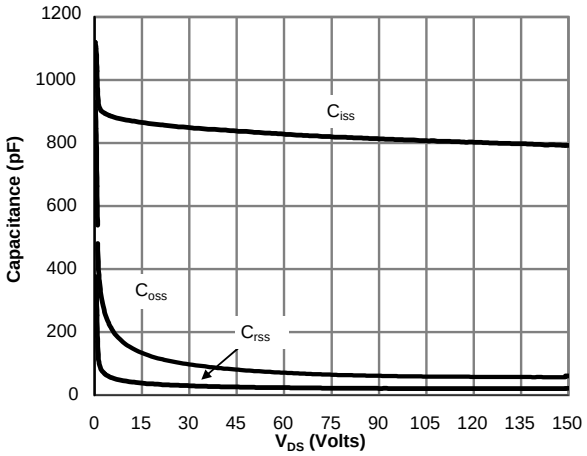


Figure 8: Capacitance Characteristics

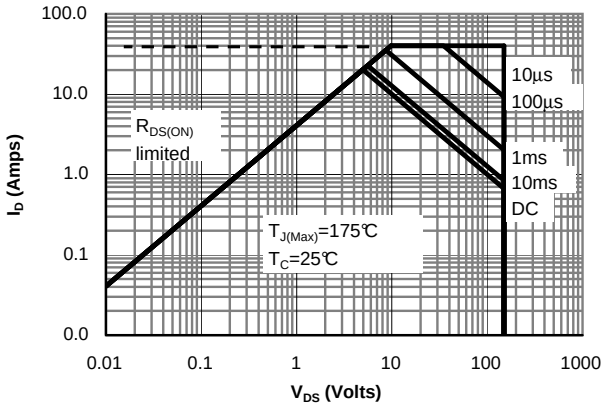


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

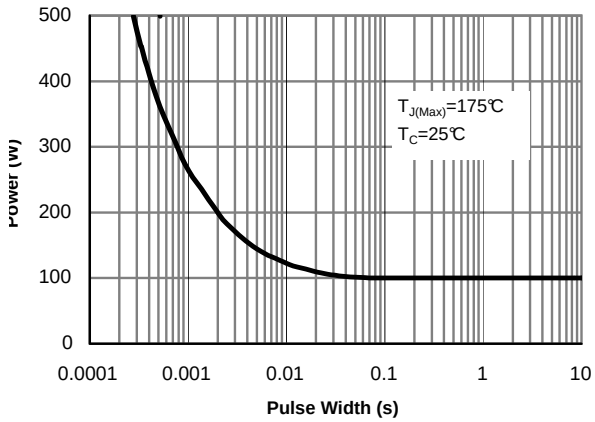


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

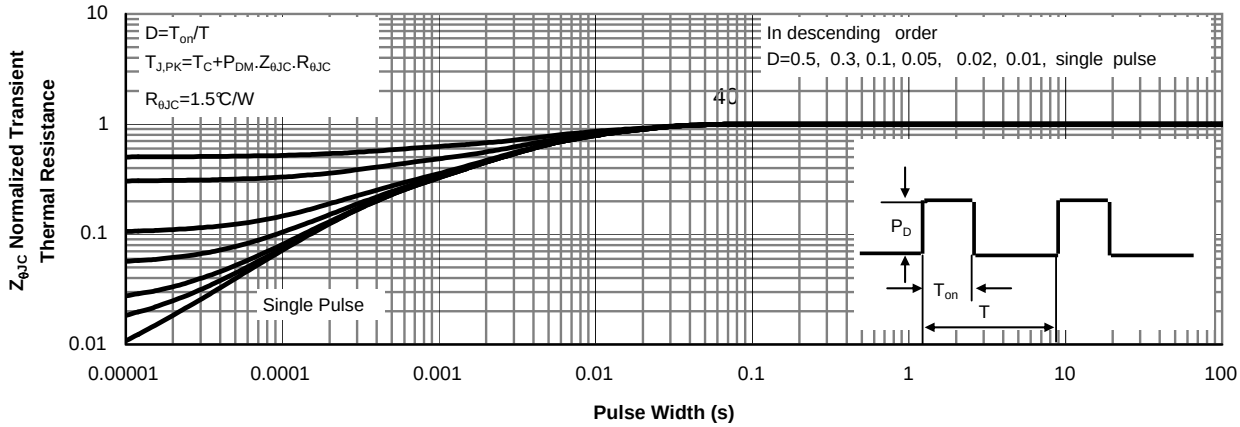


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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